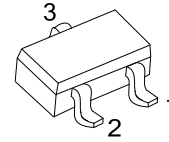
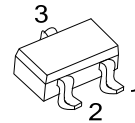


**BC807/BC808****PNP SILICON TRANSISTOR****SWITCHING AND AMPLIFIER APPLICATIONS****■ FEATURES**

- * Suitable for AF-Driver stages and low power output stages
- * Complement to BC817 / BC818

**SOT-23**
(JEDEC TO-236)**SOT-323****■ ORDERING INFORMATION**

Ordering Number	Package	Pin Assignment			Packing
		1	2	3	
BC807G-xx-AE3-R	SOT-23	E	B	C	Tape Reel
BC807G-xx-AL3-R	SOT-323	E	B	C	Tape Reel
BC808G-xx-AE3-R	SOT-23	E	B	C	Tape Reel
BC808G-xx-AL3-R	SOT-323	E	B	C	Tape Reel

Note: Pin Assignment: C: Collector B: Base E: Emitter

	(1)Packing Type	(1) R: Tape Reel
	(2)Package Type	(2) AE3: SOT-23, AL3: SOT-323
	(3)Rank	(3) xx: refer to Classification of h _{FE}
	(4)Green Package	(4) G: Halogen Free and Lead Free

■ MARKING

807-16	807-25	807-40
808-16	808-25	808-40

BC807/BC808

PNP SILICON TRANSISTOR

■ ABSOLUTE MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Emitter Voltage	BC807	V_{CES}	-50	V
	BC808		-30	V
Collector-Emitter Voltage	BC807	V_{CEO}	-45	V
	BC808		-25	V
Emitter-Base Voltage		V_{EBO}	-5	V
Collector Current (DC)		I_C	-800	mA
Collector Dissipation		P_C	310	mW
Junction Temperature		T_J	+150	$^{\circ}\text{C}$
Storage Temperature		T_{STG}	-65 ~ +150	$^{\circ}\text{C}$

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

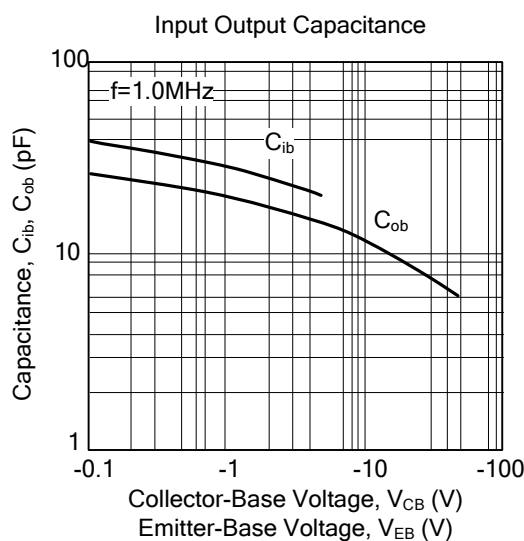
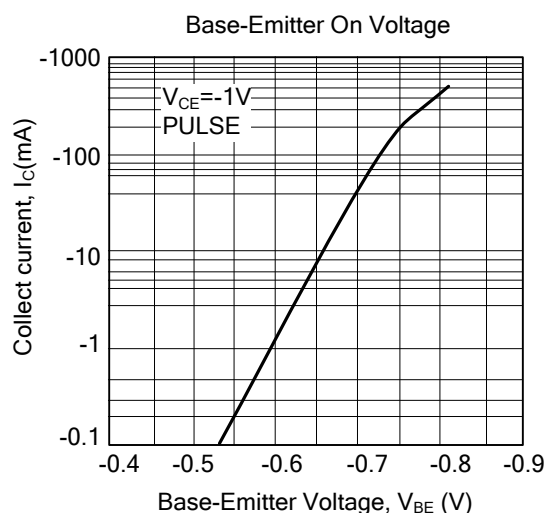
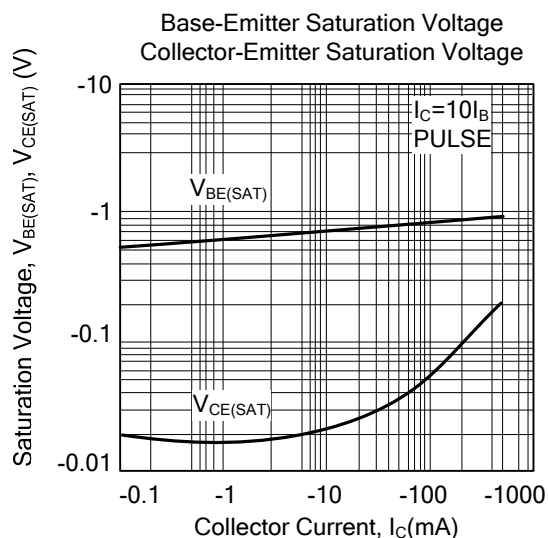
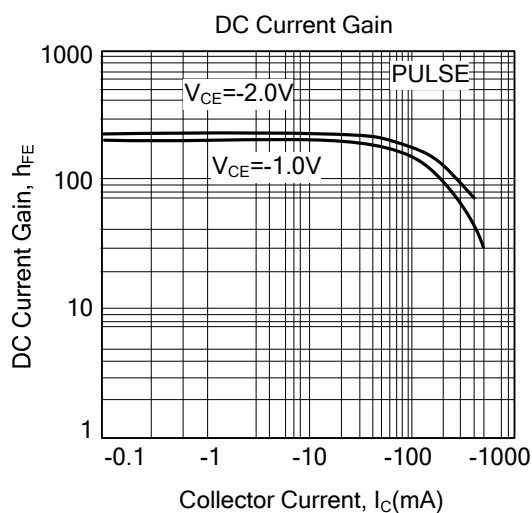
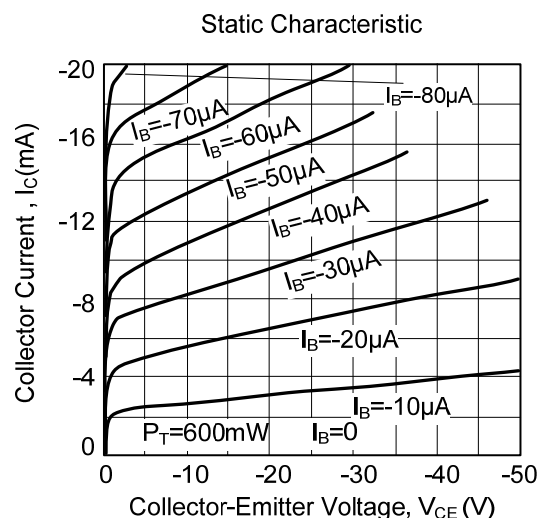
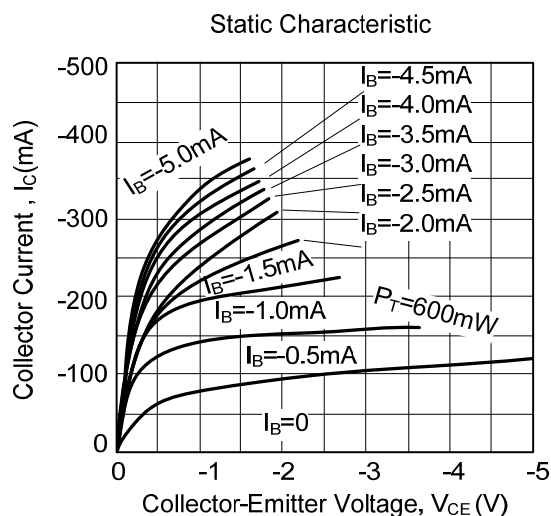
■ ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$, unless otherwise noted)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Emitter Breakdown Voltage	BC807	BV _{CEO}	I _C =-10mA, I _B =0	-45			V
	BC808			-25			V
Collector-Emitter Breakdown Voltage	BC807	BV _{CES}	I _C =-0.1mA, V _{BE} =0	-50			V
	BC808			-30			V
Emitter-Base Breakdown Voltage		BV _{EBO}	I _E =-0.1mA, I _C =0	-5			V
Collector Cut-OFF Current		I _{CES}	V _{CE} =-25V, V _{BE} =0			-100	nA
Emitter Cut-OFF Current		I _{EBO}	V _{EB} =-4V, I _C =0			-100	nA
DC Current Gain		h _{FE1}	I _C =-100mA, V _{CE} =-1V	100		630	
		h _{FE2}	I _C =-300mA, V _{CE} =-1V	60			
Collector-Emitter Saturation Voltage		V _{CE(SAT)}	I _C =-500mA, I _B =-50mA			-0.7	V
Base-Emitter ON Voltage		V _{BE(ON)}	I _C =-300mA, V _{CE} =-1V			-1.2	V
Current Gain Bandwidth Product		f _T	V _{CE} =-5V, I _C =-10mA, f=50MHz		100		MHz
Output Capacitance		C _{ob}	V _{CB} =-10V, f=1MHz			12	pF

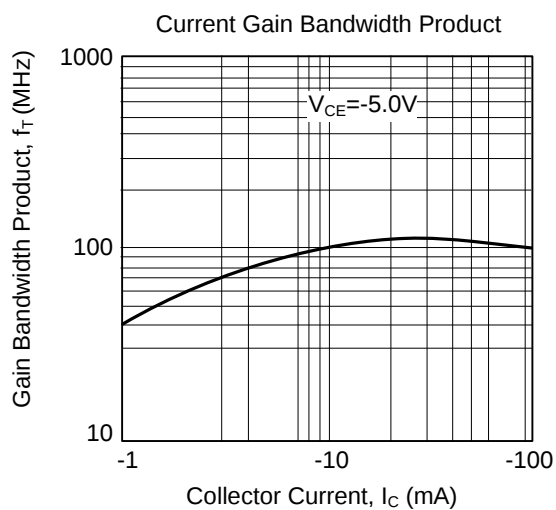
■ CLASSIFICATION OF h_{FE}

RANK	16	25	40
h_{FE1}	100-250	160-400	250-630
h_{FE2}	60-	100-	170-

TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS(Cont.)



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